

L Number	Hits	Search Text	DB	Time stamp
1	2181	(TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches)	USPAT; EPO; JPO; IBM_TDB	2003/07/22 14:26
2	1702	(TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist)	USPAT; EPO; JPO; IBM_TDB	2003/07/22 14:27
4	35	(TEOS or "tetra ethyl ortho silicate") same (implanted or implanting or implantation) same (boron or phosphorus) same (HF or vapor or hydrofluoric) same (contact or opening or trenches) and (resist or photoresist)	USPAT; EPO; JPO; IBM_TDB	2003/07/22 14:31
5	1702	(TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist)	USPAT; EPO; JPO; IBM_TDB	2003/07/22 15:03
6	2065	dual adj damascene	USPAT; EPO; JPO; IBM_TDB	2003/07/22 14:34
7	39	((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist)) and (dual adj damascene)	USPAT; EPO; JPO; IBM_TDB	2003/07/22 14:34
8	1		USPAT	2003/07/22 14:38
9	1642	(TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor	USPAT; EPO; JPO; IBM_TDB	2003/07/22 16:03
10	1184	((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls.	USPAT; EPO; JPO; IBM_TDB	2003/07/22 15:05
11	856	(TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor	USPAT; EPO; JPO; IBM_TDB	2003/07/22 15:09
12	65	(TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor and (second adj opening)	USPAT; EPO; JPO; IBM_TDB	2003/07/22 15:34
13	856	(TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor	USPAT; EPO; JPO; IBM_TDB	2003/07/22 16:01

14	948	(stacked or stack or stacking) same implant\$3 same (opening or contact or trenches)	USPAT; EPO; JPO; IBM_TDB	2003/07/22 16:02
15	280	((stacked or stack or stacking) same implant\$3 same (opening or contact or trenches)) and (boron or phosphorus) and (HF or vapor)	USPAT; EPO; JPO; IBM_TDB	2003/07/22 16:03